

TOSHIBA TRANSISTOR SILICON, SILICON GERMANIUM NPN EPITAXIAL PLANAR TYPE

MT6L76FS

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Two devices are built in to the fine pitch small mold package (6pins):fs6

- It excels in the buffer and oscillation use.
- Lead (Pb)-free.

Mounted Devices

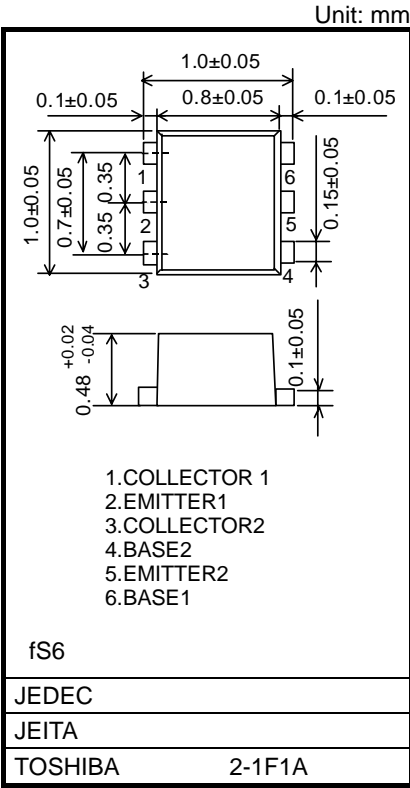
	Q1	Q2
Three-pin fSM mold products are corresponded	MT3S06FS	MT3S106FS

Maximum Ratings (Ta = 25°C)

CHARACTERISTICS	SYMBOL	RATING		UNIT
		Q1	Q2	
Collector-Base Voltage	V _{CBO}	10	13	V
Collector-Emitter Voltage	V _{CEO}	5	6	V
Emitter-Base Voltage	V _{EBO}	1.5	1	V
Collector Current	I _C	15	80	mA
Base Current	I _B	7	20	mA
		100		
		110 (Note 2)		
Junction temperature	T _j	125		°C
Storage temperature range	T _{stg}	-55~125		°C

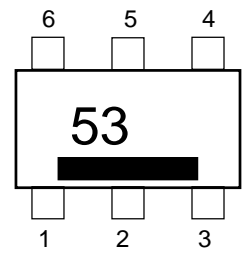
Note 1 : 1.0 cm² × 1.0 mm (t) at the time of glass epoxy printed circuit board mounting.

Note 2 : At the time of two-element operation

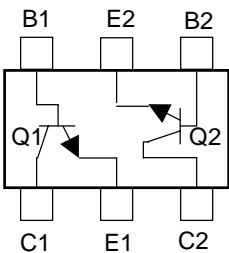


Weight : 0.001g (typ.)

Marking (top view)



Pin Assignment (top view)



ELECTRICAL CHARACTERISTICS Q1 (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	70	—	140	—
Reverse Transfer Capacitance	C_{re} (Note)	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.25	0.5	pF
Transition Frequency	f_T	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}$	7	10	—	GHz
Insertion Gain	$ S_{21e} ^2$ (1)	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$	—	8.5	—	dB
	$ S_{21e} ^2$ (2)	$V_{CE} = 3\text{ V}, I_C = 7\text{ mA}, f = 2\text{ GHz}$	7	9.5	—	
Noise Figure	NF	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$	—	1.7	3	dB

ELECTRICAL CHARACTERISTICS Q2 (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	0.5	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	110	—	160	—
Reverse Transfer Capacitance	C_{re} (Note)	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.5	0.7	pF
Transition Frequency	f_T	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}$	6.5	8.5	—	GHz
Insertion Gain	$ S_{21e} ^2$ (1)	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}, f = 2\text{ GHz}$	—	8	—	dB
	$ S_{21e} ^2$ (2)	$V_{CE} = 3\text{ V}, I_C = 20\text{ mA}, f = 2\text{ GHz}$	8.5	10	—	
Noise Figure	NF	$V_{CE} = 1\text{ V}, I_C = 10\text{ mA}, f = 2\text{ GHz}$	—	1.2	2	dB

Note : C_{re} is measured by 3 terminal method capacitance bridge.

Caution

This device is sensitive to electrostatic discharge due to applied the high frequency transistor process of

$f_T=60\text{GHz}$ class is used for this product.

Please make enough tool and equipment earthed when you handle.

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